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INFORMATION DISCLOSURE STATEMENT

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Applicant
Hisashi OHTANI et al.

Filing Date
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Serial No.
08/479,211

U. S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

OTHER DOCUMENTS (including)	
CR	C. Hayzelden et al., "In Situ Transmission Electron Microscopy Studies of Silicide-Mediated Crystallization of Amorphous Silicon" (3 pages) <u>Appl. PHYS. lett.</u> 60(1992)225
UR	A.V. Dvurechenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals" <u>Akademik Lavrentev Preprint</u> 13 630000 Novosibirsk 90 USSR, pp. 635-640. <u>PHYS. STAT. SOL. A</u> 95(1986)635
UR	T. Hempel et al., "Needle-Like Crystallization of Ni Doped Amorphous Silicon Thin Films", <u>Solid State Communications</u> , Vol. 85, No. 11, pp. 921-924, 1993.

Examiner

L Ransom

Date Considered

2/22/96

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

